Revision. 2

MOS FET

SK8403160L

Panasonic

SK8403160L

Silicon N-channel MOS FET

For Load-switching / For DC-DC Converter

■ Features

- Low Drain-source On-state Resistance : RDS(on) typ = 3.2 m Ω (VGS = 4.5 V)
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL : Level 1 compliant)
- Marking Symbol : 16

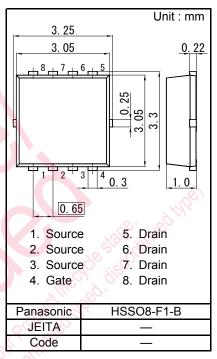
■ Packaging

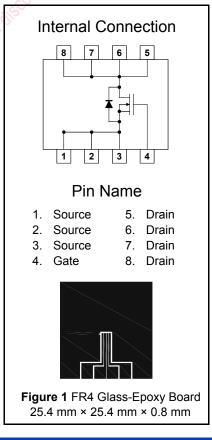
Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

Parameter			Unit	
Drain to Source Voltage			V	
Gate to Source Voltage			V	
Ta = 25 °C, t = 10 s *1			ille	
Ta = 25 °C, DC *1		18	110/10, 09	
25 °C	ווי	70	OllA	
ed, Tch < 150 °C *2		87	biological	
Ta = 25 °C, DC *1	DD	2 ///	w w	
Tc = 25 °C	FU	28	3, vv	
Channel to Ambient	Rth(ch-a)	62.5	°C / W	
Channel to Case	Rth(ch-c)	4.5	-0 / ٧٧	
Channel Temperature				
Operating ambient temperature			°C	
Storage Temperature Range				
Avalanche Current (Single pulse) *3		14.5	Α	
Avalanche Energy (Single pulse) *3		26	mJ	
	age 25 °C, t = 10 s *1 25 °C, DC *1 25 °C ed, Tch < 150 °C *2 Ta = 25 °C, DC *1 Tc = 25 °C Channel to Ambient Channel to Case e emperature e Range Single pulse) *3	age VDS yge VGS $25 ^{\circ}\text{C}$, $t = 10 ^{\circ}\text{S}^{-1}$ $25 ^{\circ}\text{C}$, $DC ^{\circ}\text{S}^{-1}$ $25 ^{\circ}\text{C}$ add, $Tch < 150 ^{\circ}\text{C}^{-2}$ Ta = 25 $^{\circ}\text{C}$, $DC ^{\circ}\text{S}^{-1}$ Tc = 25 $^{\circ}\text{C}$ Channel to Ambient Rth(ch-a) Channel to Case Rth(ch-c) e Tch e Range Tstg Single pulse) Tstg IAR	age VDS 30 ge VGS ±20 25 °C, t = 10 s *1 25 °C, DC *1 10 25 °C 27 Ta = 25 °C, DC *1 Tc = 25 °C Channel to Ambient Rth(ch-a) Channel to Case Rth(ch-c) E Range Tstg -55 to +150 Single pulse) *3 NGS ±20 29 29 27 70 20 20 21 28 28 Channel to Ambient Rth(ch-a) 62.5 Channel to Case Rth(ch-c) 4.5 4.5 4.5 4.5 4.5 4.5 4.5 4.	

- Note *1 Device mounted on a glass-epoxy board in Figure 1
 - *2 Pulse test: Ensure that the channel temperature does not exceed 150 °C
 - *3 VDD = 24 V, VGS = 10 to 0 V, L = 0.1 mH, Tch = 25 °C (initial)





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■ Electrical Characteristics Ta = 25 °C ± 3 °C

Static Characteristics

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source Breakdown Voltage	VDSS	ID = 1 mA, VGS = 0 V	30			V
Zero Gate Voltage Drain Current	IDSS	VDS = 30 V, VGS = 0 V			10	μΑ
Gate-source Leakage Current	IGSS	VGS = ± 16 V, VDS = 0 V			±10	μΑ
Gate-source Threshold Voltage	Vth	ID = 3.35 mA, VDS = 10 V	1.3		3	V
I Irain-collect i in-ctata Pacietanca	, ,	ID = 14.5 A, VGS = 10 V		2.5	3.3	mΩ
	RDS(on)2	ID = 14.5 A, VGS = 4.5 V		3.2	4.3	

Dynamic Characteristics

By Harrie Characteriotics						
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Input Capacitance	Ciss	VDS = 10 V, VGS = 0 V		2 800	3 920	
Output Capacitance	Coss	f = 1 MHz		330	470	pF
Reverse Transfer Capacitance	Crss	1 - 1 IVITIZ		230	370	
Turn-on Delay Time *1	td(on)	VDD = 15 V, VGS = 0 to 10 V		13	2. 0) no
Rise Time *1	tr	ID = 14.5 A		12	J. Wille	ns
Turn-off Delay Time *1	td(off)	VDD = 15 V, VGS = 10 to 0 V		52	1/1/1	no
Fall Time *1	tf	ID = 14.5 A	-10	8		ns
Total Gate Charge	Qg	VDD = 15 V, VGS = 0 to 4.5 V	ررون	22		
Gate to Source Charge	Qgs	ID = 14.5 A	111.	7 7		nC
Gate to Drain Charge	Qgd	ID - 14.5 A	JET !	9		
Gate resistance	rg	f = 5 MHz	80	1.2	3	Ω

Body Diode Characteristic

Established: 2013-01-07

Revised

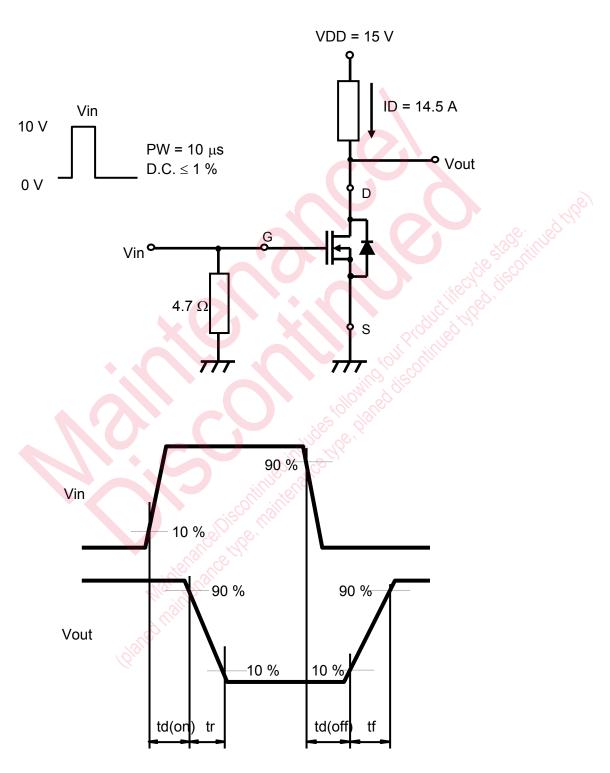
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Diode Forward Voltage	VSD	IS = 14.5 A, VGS = 0 V		0.8	1.2	V

Note: 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

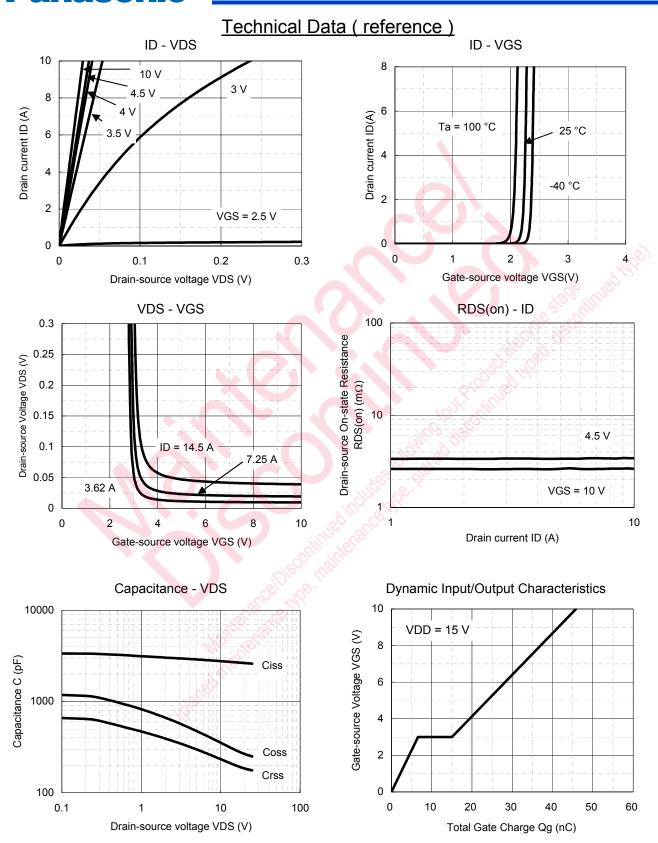
2. *1 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time

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*1 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time

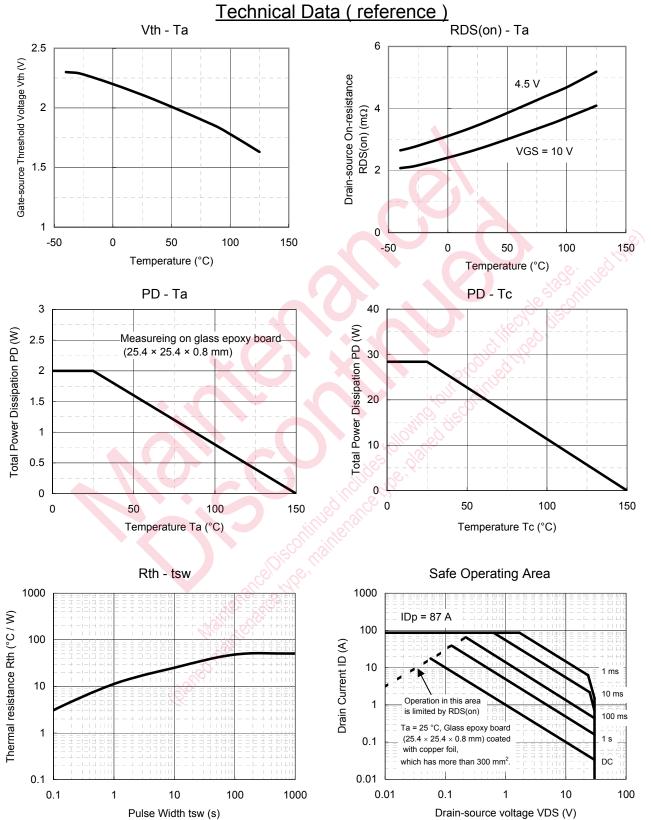


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5K84U3 10UL



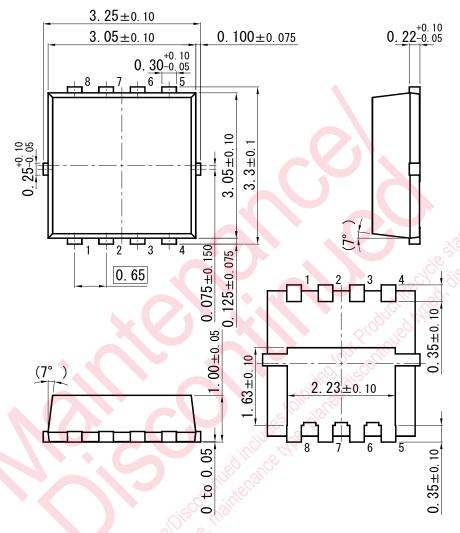
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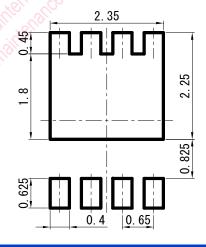
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HSSO8-F1-B

Unit: mm



■ Land Pattern (Reference) (Unit: mm)



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